

CLAIM AMENDMENTS:

Please cancel Claims 2 and 11, and amend Claims 1, 3, 7 and 9 as follows:

1. (Currently Amended) A field effect transistor comprising:
a substrate comprising a source region and a drain region;
an insulating layer arranged on the substrate; and
a porous body which has pillar-shaped holes arranged on the insulating layer, wherein ~~the porous body includes a semiconductor material~~ the insulating layer is formed between the substrate and the porous body.
2. (Cancelled)
3. (Currently Amended) The field-effect transistor according to Claim [[2]] 1, characterized in that the porous [[film]] body is composed of an insulating material or a semiconductor material.
4. (Original) The field-effect transistor according to Claim 3, characterized in that the semiconductor material is a material which uses silicon, germanium, or silicon and germanium as a main component.
5. (Original) The field-effect transistor according to Claim 3, characterized in that the insulating material is a material which uses silicon oxide as a main component.
6. (Original) The field-effect transistor according to Claim 1, characterized in that average pore diameter of the pillar-shaped pores is 20 nm or less, and mean pore density is 1.5×10^{11} pores/cm² or more.

7. (Currently Amended) The field-effect transistor according to Claim 1, having on surfaces of the pillar-shaped pores a ~~detected~~ detection material for detecting a specific ~~detection~~ detected material.

8. (Original) The field-effect transistor according to Claim 7, characterized in that the detection material is a biomaterial.

9. (Currently Amended) The field-effect transistor according to Claim 6, characterized in that the detection material causes a change of an electric charge state by contacting with ~~[[a]]~~ the detected material.

10. (Original) A sensor using the field-effect transistor according to Claim 1.

11. (Cancelled)